

Please replace the abstract with the following amended abstract:

A semiconductor device having bump electrodes electrically connected to connection pads formed on a semiconductor chip of the semiconductor device, tips of the bump electrodes ~~exposing~~ being exposed at a surface of a sealing resin film formed on a surface of the semiconductor chip, wherein the sealing resin film is comprised of a low-elastic resin layer formed on the surface of the semiconductor chip and a high-elastic resin layer formed on a surface of the low-elastic resin layer and having an elastic coefficient higher than that of the low-elastic resin layer, a thickness of the high-elastic resin layer being between 5 μm and 45 μm .